

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 40201	SERIAL NO. TBD 10574863
INFORMATION DISCLOSURE CITATION BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT: Yuichiro Sasaki et al.	
		FILING DATE: Herewith 04/06/2006	GROUP ART UNIT: TBD 2823

U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Name	Class	Subclass	Filing Date If Appropriate
	A						
	B						
	C						
	D						
	E						
	F						
	G						

FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Class	Subclass	Translation
	H	5-206053	08/1993	JAPAN			Cited on ISR
	I	9-17867	01/1997	JAPAN			Cited on ISR
	J	2003-528462	09/2003	JAPAN			Cited on ISR
	K						

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

/PG/	L	Talwar et al., "Study of Laser Thermal Processing (LPT) to Meet Sub 130 nm Node Shallow Junction Requirements", 2000, pages 175-177 (Cited in Specification)
/PG/	M	Ito et al., "Flash Lamp Annealing Technology for Ultra-shallow Junction Formation", Extended Abstract of International Workshop on Junction Technology, 2002, pages 23-26 (Cited in Specification)
/PG/	N	Yamamoto et al., "Impact of Pre-Amorphization for the Reduction of Contact Resistance Using Laser Thermal Process", Extended Abstract of International Workshop on Junction Technology, 2002, pages 27-30 (Cited in Specification)
/PG/	O	Kagawa et al., "Influence of Pulse Duration on KrF Excimer Laser Annealing Process for Ultra Shallow Junction Formation, Extended Abstract of International Workshop on Junction Technology, 2002, pages 31-34 (Cited in Specification)
/PG/	P	Ito et al., "Improvement of Threshold Voltage Roll-off by Ultra-shallow Junction Formed by Flash Lamp Annealing", 2003, pages 53-54 (Cited in Specification)

Examiner: /Phillip Green/	Date Considered 09/03/2007
------------------------------	-------------------------------

*Examiner: Initial if reference considered, regardless of whether citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.